

**FAIRCHILD**  
SEMICONDUCTOR®

**IGBT**

## SGH25N120RUF

### Short Circuit Rated IGBT

#### General Description

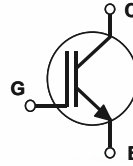
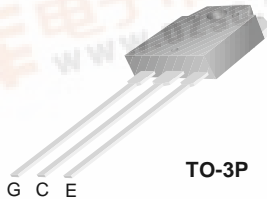
Fairchild's RUF series of Insulated Gate Bipolar Transistors (IGBTs) provides low conduction and switching losses as well as short circuit ruggedness. The RUF series is designed for applications such as motor control, uninterrupted power supplies (UPS) and general inverters where short circuit ruggedness is a required feature.

#### Features

- Short circuit rated 10 $\mu$ s @ T<sub>C</sub> = 100°C, V<sub>GE</sub> = 15V
- High speed switching
- Low saturation voltage : V<sub>CE(sat)</sub> = 2.3 V @ I<sub>C</sub> = 25A
- High input impedance

#### Applications

AC & DC motor controls, general purpose inverters, robotics, and servo controls.



#### Absolute Maximum Ratings

T<sub>C</sub> = 25°C unless otherwise noted

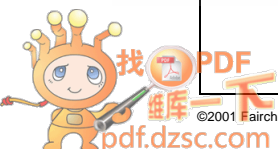
Symbol	Description	SGH25N120RUF	Units
V <sub>CES</sub>	Collector-Emitter Voltage	1200	V
V <sub>GES</sub>	Gate-Emitter Voltage	± 25	V
I <sub>C</sub>	Collector Current @ T <sub>C</sub> = 25°C	40	A
	Collector Current @ T <sub>C</sub> = 100°C	25	A
I <sub>CM(1)</sub>	Pulsed Collector Current	75	A
T <sub>SC</sub>	Short Circuit Withstand Time @ T <sub>C</sub> = 100°C	10	μs
P <sub>D</sub>	Maximum Power Dissipation @ T <sub>C</sub> = 25°C	270	W
	Maximum Power Dissipation @ T <sub>C</sub> = 100°C	108	W
T <sub>J</sub>	Operating Junction Temperature	-55 to +150	°C
T <sub>stg</sub>	Storage Temperature Range	-55 to +150	°C
T <sub>L</sub>	Maximum Lead Temp. for soldering Purposes, 1/8" from case for 5 seconds	300	°C

#### Notes :

(1) Repetitive rating : Pulse width limited by max. junction temperature

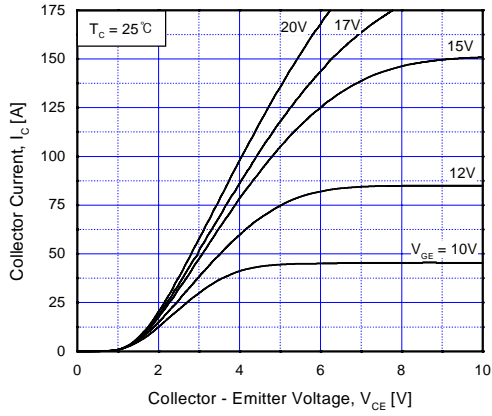
#### Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Units
R <sub>θJC</sub>	Thermal Resistance, Junction-to-Case	--	0.46	°C/W
R <sub>θJA</sub>	Thermal Resistance, Junction-to-Ambient	--	40	°C/W

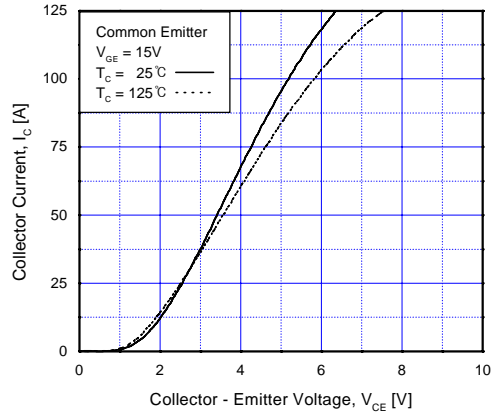


## Electrical Characteristics of the IGBT T<sub>C</sub> = 25°C unless otherwise noted

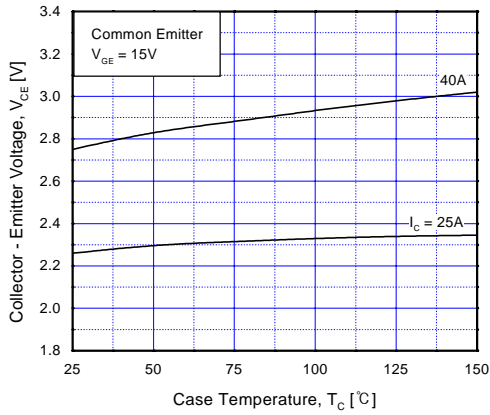
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
<b>Off Characteristics</b>						
$BV_{CES}$	Collector-Emitter Breakdown Voltage	$V_{GE} = 0V, I_C = 1mA$	1200	--	--	V
$\Delta B_{V_{CES}} / \Delta T_J$	Temperature Coefficient of Breakdown Voltage	$V_{GE} = 0V, I_C = 1mA$	--	0.6	--	V/°C
$I_{CES}$	Collector Cut-Off Current	$V_{CE} = V_{CES}, V_{GE} = 0V$	--	--	1	mA
$I_{GES}$	G-E Leakage Current	$V_{GE} = V_{GES}, V_{CE} = 0V$	--	--	± 100	nA
<b>On Characteristics</b>						
$V_{GE(th)}$	G-E Threshold Voltage	$I_C = 25mA, V_{CE} = V_{GE}$	3.5	5.5	7.5	V
$V_{CE(sat)}$	Collector to Emitter Saturation Voltage	$I_C = 25A, V_{GE} = 15V$	--	2.3	2.7	V
		$I_C = 40A, V_{GE} = 15V$	--	2.8	--	V
<b>Dynamic Characteristics</b>						
$C_{ies}$	Input Capacitance	$V_{CE} = 30V, V_{GE} = 0V, f = 1MHz$	--	2400	--	pF
$C_{oes}$	Output Capacitance		--	220	--	pF
$C_{res}$	Reverse Transfer Capacitance		--	70	--	pF
<b>Switching Characteristics</b>						
$t_{d(on)}$	Turn-On Delay Time	$V_{CC} = 600V, I_C = 25A, R_G = 10\Omega, V_{GE} = 15V, \text{Inductive Load}, T_C = 25^\circ C$	--	30	--	ns
$t_r$	Rise Time		--	60	--	ns
$t_{d(off)}$	Turn-Off Delay Time		--	70	130	ns
$t_f$	Fall Time		--	150	200	ns
$E_{on}$	Turn-On Switching Loss		--	1.60	--	mJ
$E_{off}$	Turn-Off Switching Loss		--	1.63	--	mJ
$E_{ts}$	Total Switching Loss	--	3.23	4.55	mJ	
$t_{d(on)}$	Turn-On Delay Time	$V_{CC} = 600V, I_C = 25A, R_G = 10\Omega, V_{GE} = 15V, \text{Inductive Load}, T_C = 125^\circ C$	--	30	--	ns
$t_r$	Rise Time		--	70	--	ns
$t_{d(off)}$	Turn-Off Delay Time		--	90	165	ns
$t_f$	Fall Time		--	200	270	ns
$E_{on}$	Turn-On Switching Loss		--	1.88	--	mJ
$E_{off}$	Turn-Off Switching Loss		--	2.50	--	mJ
$E_{ts}$	Total Switching Loss	--	4.35	6.31	mJ	
$T_{sc}$	Short Circuit Withstand Time	$V_{CC} = 600V, V_{GE} = 15V @ T_C = 100^\circ C$	10	--	--	μs
$Q_g$	Total Gate Charge	$V_{CE} = 600V, I_C = 25A, V_{GE} = 15V$	--	110	165	nC
$Q_{ge}$	Gate-Emitter Charge		--	18	27	nC
$Q_{gc}$	Gate-Collector Charge		--	55	83	nC
$L_e$	Internal Emitter Inductance	Measured 5mm from PKG	--	14	--	nH



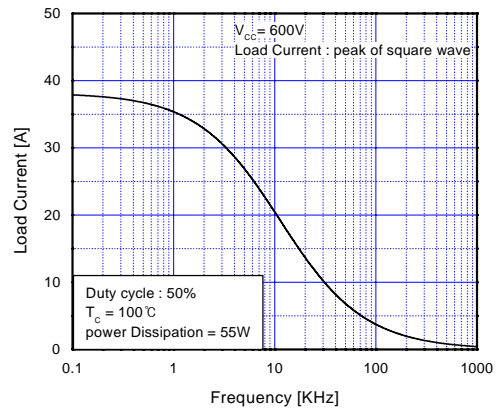
**Fig 1. Typical Output Characteristics**



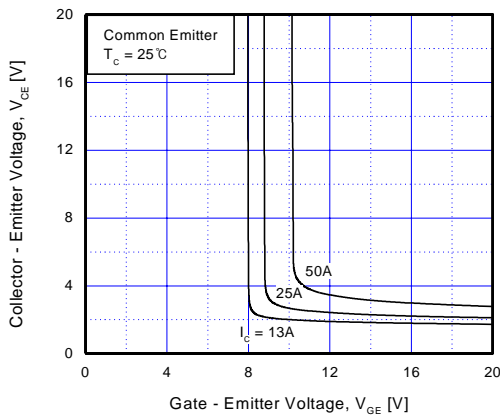
**Fig 2. Typical Saturation Voltage Characteristics**



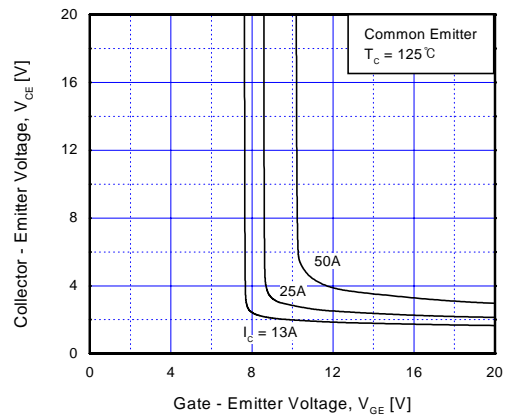
**Fig 3. Saturation Voltage vs. Case Temperature at Variant Current Level**



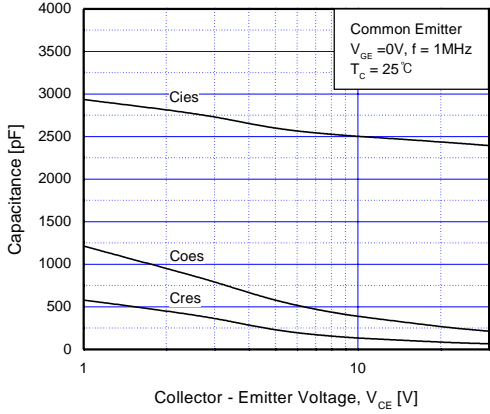
**Fig 4. Load Current vs. Frequency**



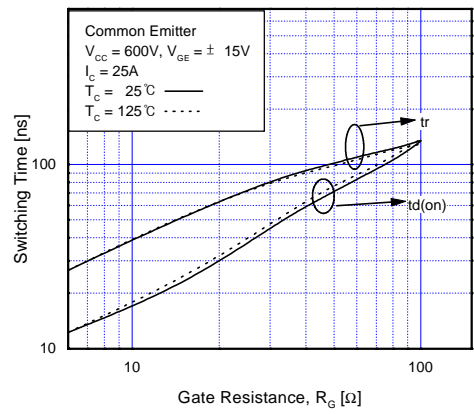
**Fig 5. Saturation Voltage vs.  $V_{GE}$**



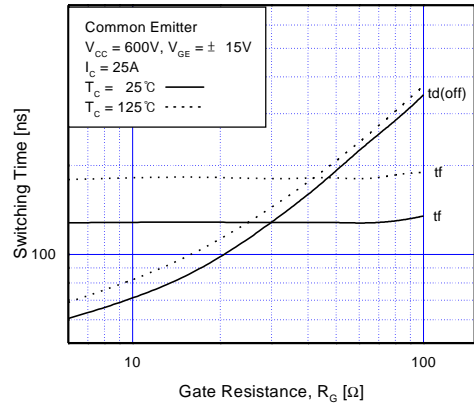
**Fig 6. Saturation Voltage vs.  $V_{GE}$**



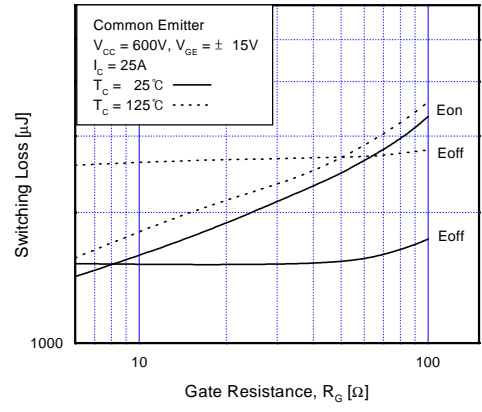
**Fig 7. Capacitance Characteristics**



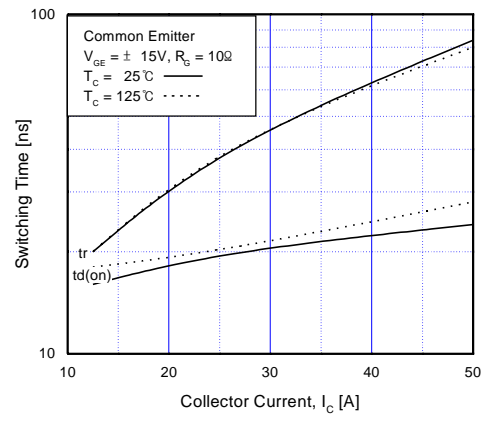
**Fig 8. Turn-On Characteristics vs. Gate Resistance**



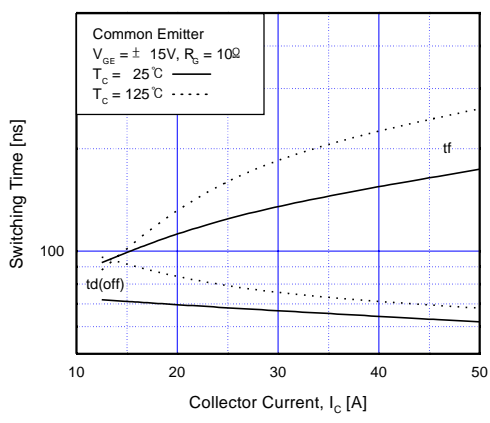
**Fig 9. Turn-Off Characteristics vs. Gate Resistance**



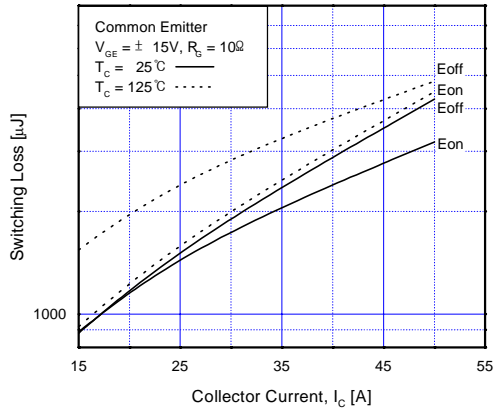
**Fig 10. Switching Loss vs. Gate Resistance**



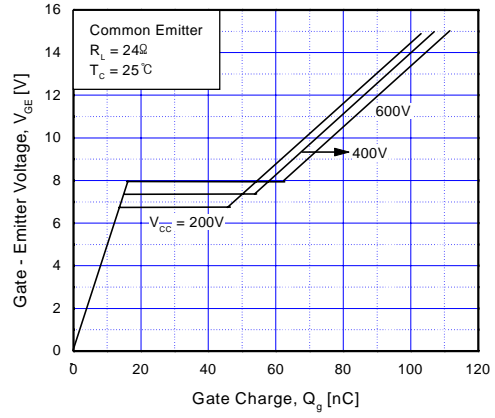
**Fig 11. Turn-On Characteristics vs. Collector Current**



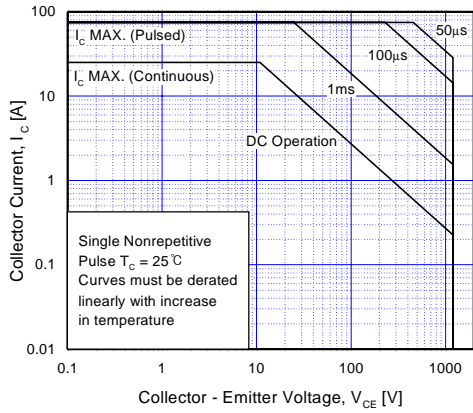
**Fig 12. Turn-Off Characteristics vs. Collector Current**



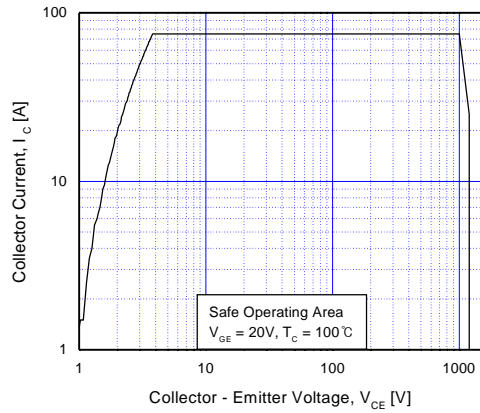
**Fig 13. Switching Loss vs. Collector Current**



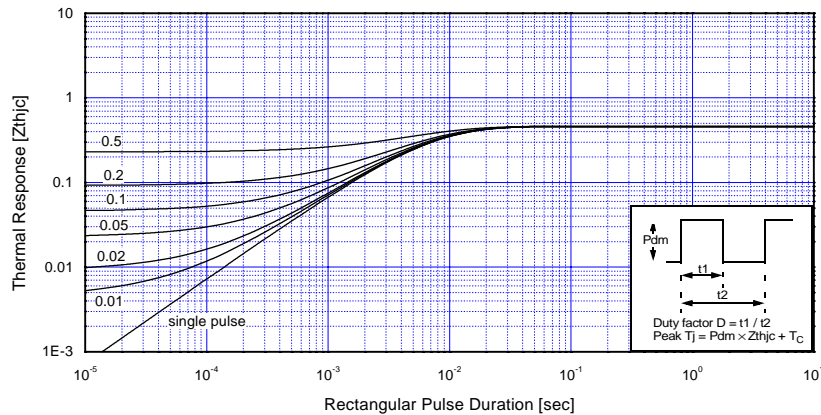
**Fig 14. Gate Charge Characteristics**



**Fig 15. SOA Characteristics**



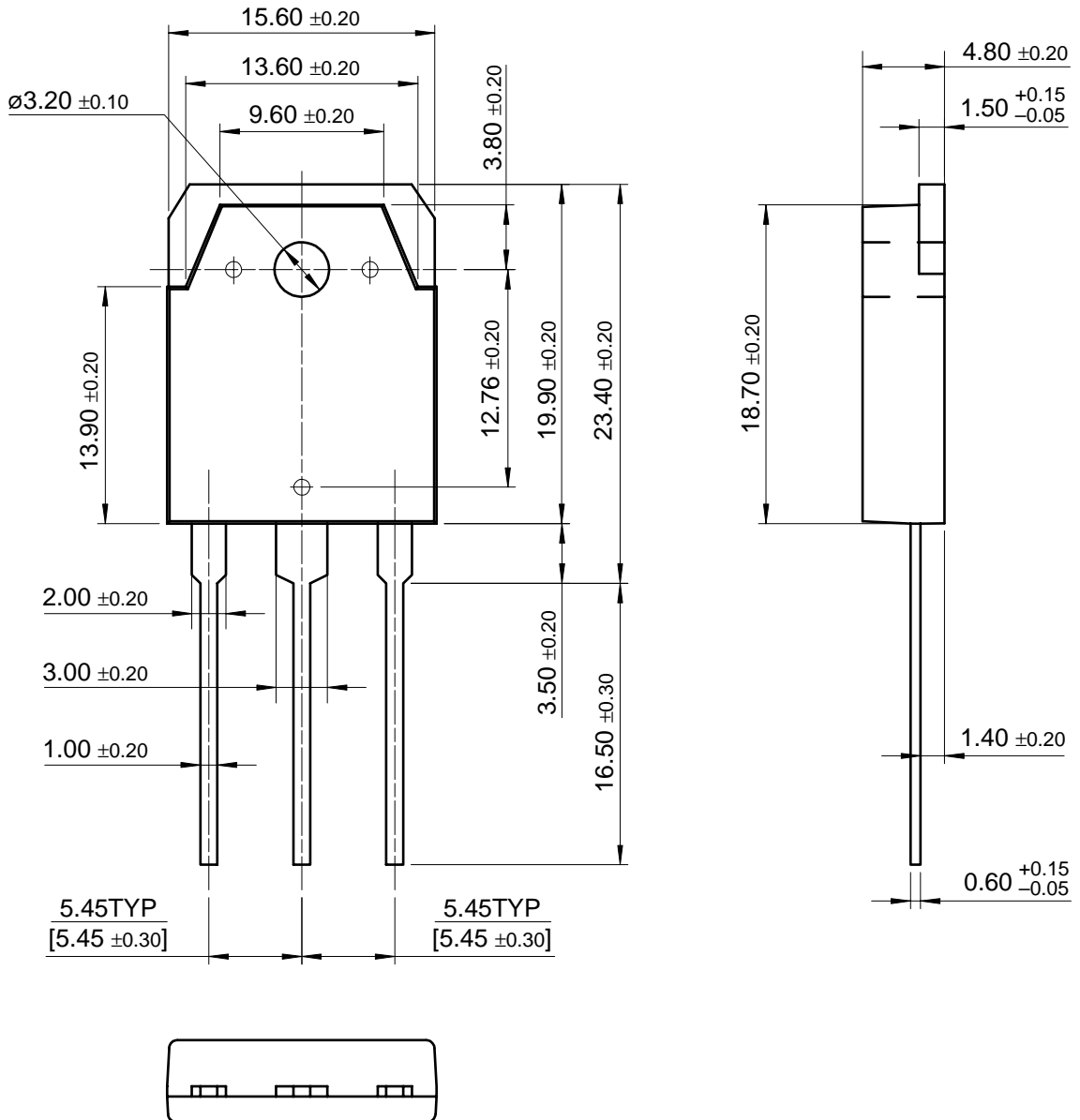
**Fig 16. Turn-Off SOA**



**Fig 17. Transient Thermal Impedance of IGBT**

Package Dimension

TO-3P (FS PKG CODE AF)



Dimensions in Millimeters

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